

ABSTRACT

ALUMINUM NITRIDE SINTERED BODY AND MEMBER FOR
SEMICONDUCTOR MANUFACTURING APPARATUS COMPRISING SAME

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An aluminum nitride sintered body contains 1 to 5%
by weight of yttrium oxide (Y_2O_3), 10 to 100 ppm by
weight of titanium (Ti), and the balance being aluminum
nitride (AlN). Accordingly, a volume resistance value
10 and thermal conductivity at a high temperature are
improved, and the generation of impurities during a
semiconductor manufacturing process can be suppressed.